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TITLE: THIN FILM TRANSISTOR AND THIN FILM INTEGRATED ELEMENT

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INVENTOR-INFORMATION:

NAME	COUNTRY
SERA, KENJI	N/A

ASSIGNEE-INFORMATION:

NAME	COUNTRY
NEC CORP	N/A

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ABSTRACT:

PROBLEM TO BE SOLVED: To obtain a thin film transistor and a thin film integrated element exhibiting excellent heat dissipation properties in which permeation of impurities from a glass substrate is prevented.

SOLUTION: A substrate insulation film 2, a p-Si semiconductor layer 3, an SiO₂ gate insulation film 4, a gate electrode 5, and a protective insulation film 10 are formed in this order on a glass substrate 1 wherein the substrate insulation film 2 and the protective insulation film 10 are formed of alumina or aluminum nitride. Since both insulation films sandwiching an MOS transistor are made of a metal oxide or nitride having high thermal conductivity, problems of heat accumulation and impurity permeation are solved and a thin film IC can be developed.

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